

said external connection protruding electrodes forming a bump,
 said bump having a height larger than a height of said protruding electrode for a part thereof
 protruding beyond said resin layer.

110. (Twice Amended) The semiconductor device as claimed in claim 109, wherein both a side portion of the resin layer and a side portion of the semiconductor are respectively exposed.

111. (Twice Amended) A semiconductor device comprising:
 a semiconductor element having a surface on which protruding electrodes having convex end portions are formed;

 a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except the convex end portions thereof; and
 external connection protruding electrodes provided to the convex end portions of the protruding electrodes that protrude from the resin layer,

 said external connection protruding electrodes forming a bump,
 said bump having a height larger than a height of said protruding electrode for a part thereof
 protruding beyond said resin layer.

112. (Amended) The semiconductor device as claimed in claim 111, wherein both of a side portion of the resin layer and a side portion of the semiconductor element are respectively exposed.

115. (Twice Amended) A semiconductor device comprising :

a semiconductor element having a surface on which electrode pads connected to an internal part of the semiconductor element and protruding electrodes to be connected to an external part are formed;

lead lines each connecting one of the electrode pads and one of the protruding electrodes so that the protruding electrodes and the internal pad are connected through the lead lines; and

cont'd a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof,

II the protruding electrodes having a core portion and an electrically conductive film formed on a surface of the core portion,

the core portions of the protruding electrodes are directly formed on the lead lines, wherein the core portion comprises an elastic resin.

119. (Twice Amended) A semiconductor device comprising:

a semiconductor element having a surface on which electrode pads connected to an internal part of the semiconductor element and protruding electrodes to be connected to an external part are formed;

II lead lines each connecting one of the electrode pads and one of the protruding electrodes so that the protruding electrodes and the internal part are connected through the lead lines;

a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof; and

external connection protruding electrodes provided to the end portions of the protruding electrodes that protrude from the resin layer,

the protruding electrodes having a core portion and an electrically conductive film formed on a surface of the core portion,

Contd
12 the core portions of the protruding electrodes are directly formed on the lead lines, wherein the core portion comprises an elastic resin.

123. (Twice Amended) A semiconductor device as claimed in claim 127

wherein a part of a side portion of the semiconductor element being covered with the resin layer,

13 a part of a side portion of said semiconductor elements being exposed.

127. (Amended) A semiconductor device comprising:

a semiconductor element having a surface on which protruding electrodes are formed; and a compression-molded resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof,

wherein the compression-molded resin layer and the semiconductor element have surfaces defined by cutting using a dicer.

14 Please add new claims 132-135 as follows:

132. (New) A semiconductor device characterized by comprising:

a semiconductor element having protruding electrodes formed on a surface thereof;
a first resin layer that is formed on the surface of the semiconductor element and seals the protruding electrodes except for ends thereof; and
a second resin layer provided so as to cover at least a back surface of the semiconductor element,

a sidewall surface of said semiconductor element being exposed at a sidewall surface of said semiconductor device.

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133. (New) A semiconductor device as claimed in claim 132, wherein a sidewall surface of said first resin layer and a sidewall surface of said second resin layer form a flush surface with said sidewall surface of said semiconductor element.

134. (New) The semiconductor device as claimed in claim 109, wherein said resin layer is a compression-molded resin layer.

135. (New) The semiconductor device as claimed in claim 111, wherein said resin layer is a compression-molded resin layer.